IXYS

Advance Technical Information

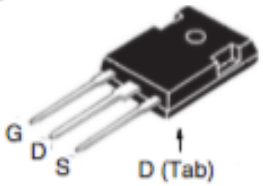
X2-Class HiPerFET™ Power MOSFET

IXFH80N65X2

V_{DSS} = 650V
I_{D25} = 80A
$R_{DS(on)}$ ≤ 40mΩ

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

TO-247



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	650	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	650	V
V_{GSS}	Continuous	±30	V
V_{GSM}	Transient	±40	V
I_{D25}	T_C = 25°C	80	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	160	A
I_A	T_C = 25°C	10	A
E_{AS}	T_C = 25°C	700	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	50	V/ns
P_D	T_C = 25°C	890	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		6	g

Features

- International Standard Package
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol (T_J = 25°C, Unless Otherwise Specified)	Test Conditions	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	650			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4mA	2.7		5.5	V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			50	µA
	T_J = 125°C			3	mA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			40	mΩ

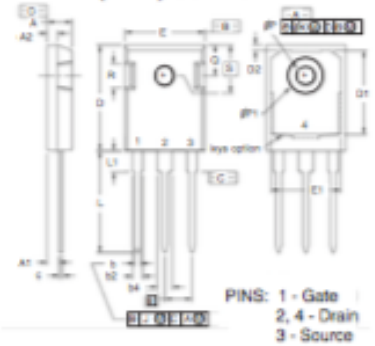
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	36	50		S
R_{Gi}	Gate Input Resistance		0.9		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		8245		pF
C_{oss}			5510		pF
C_{rss}			18		pF
$t_{d(on)}$	**Resistive Switching Times**		40		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		42		ns
$t_{d(off)}$	R_G = 2Ω (External)		60		ns
t_f			11		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		143		nC
Q_{gs}			40		nC
Q_{gd}			44		nC
R_{thJC}				0.14	°C/W
R_{thCS}			0.21		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			80	A
I_{SM}	Repetitive, pulse Width Limited by T_{JM}			320	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 40A, -di/dt = 100A/µs		185		ns
Q_{RM}	V_R = 100V		1.6		µC
I_{RM}			17		A

Note 1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.

TO-247 (IXFH) Outline



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
c	.024	.031	.61	.80
D	.819	.845	20.80	21.34
D1	.630	.696	16.00	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	---	.008	---	0.20
K	---	.035	---	.864
L	.780	.803	19.81	20.57
L1	.150	.173	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.295	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.